

## GD1SS356 SURFACE MOUNT, BAND SWITCHING DIODE VOLTAGE 35V, CURRENT 0.1A

### Description

The GD1SS356 is designed for high frequency switching application.

### Features

- High reliability
- Small mode type

### Package Dimensions

**SOD-323**

Marking :

Circuit:

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.85	1.05			
A1	0	0.10	L	0.20	0.40
A2	0.80	1.00	b	0.25	0.40
D	1.15	1.45	c	0.10	0.18
E	1.60	1.80			
HE	2.30	2.70	Q1	0.15 BSC.	

### Absolute Maximum Ratings at Ta = 25°C

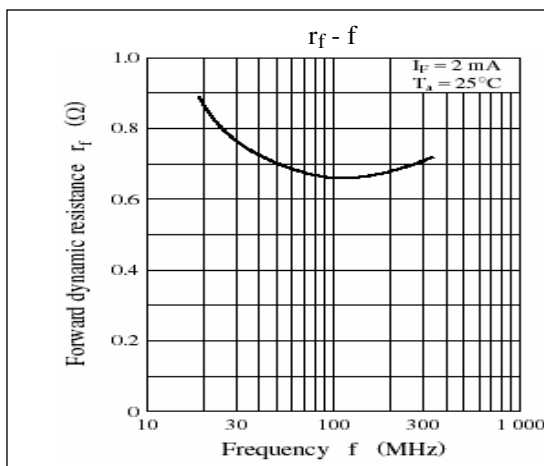
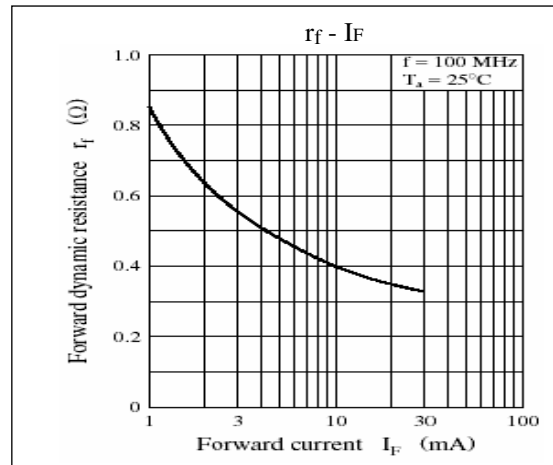
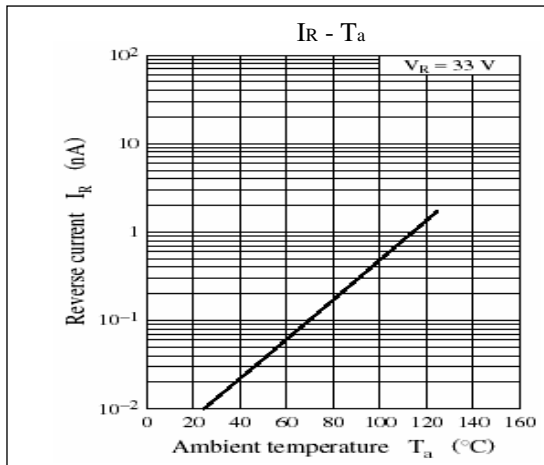
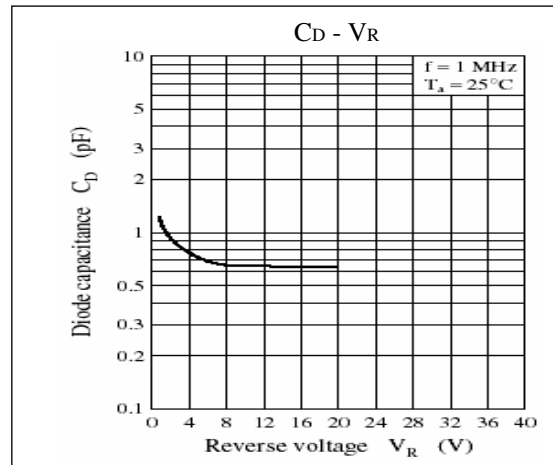
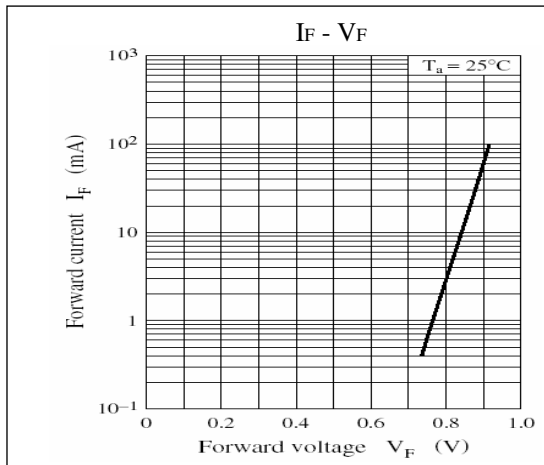
Parameter	Symbol	Ratings	Unit
Reverse Voltage(DC)	$V_R$	35	V
Forward Current(DC)	$I_F$	100	mA
Junction Temperature	$T_j$	+125	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C
Total Power Dissipation	$P_D$	225	mW

### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown	$V_R$	35	-	-	V	$I_R=10\mu A$
Reverse Current(DC)	$I_R$	-	-	10	nA	$V_R=25V$
Reverse Voltage(DC)	$V_F$	-	-	1	V	$I_F=10mA$
Diode Capacitance	$C_D$	-	0.9	1.2	pF	$V_R=6, f=1MHz$
Forward dynamic resistance	$r_f$	-	0.65	0.9	$\Omega$	$I_F=2mA, f=100MHz$

Note 1: Rated input/output frequency: 100MHz

## Characteristics Curve



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